

# P54/74FCT11373 (P54/74PCT11373) OCTAL TRANSPARENT LATCHES WITH 3-STATE OUTPUTS



## FEATURES

- Function, Pinout and Drive Compatible with the FCT, F Logic and P54/74ACT11373
- FCT speed at 3.6ns max. (Com'l)
- CMOS  $V_{OH}$  Levels for Low Power Consumption — Typically 1/3 of FAST Bipolar Logic
- Edge-rate Control Circuitry for Significantly Improved Noise Characteristics
- ESD protection exceeds 2000V
- Inputs and Outputs Interface Directly with TTL, NMOS, and CMOS Devices
- Outputs Meet Levels Required for CMOS Static RAM Low Power Standby Mode
- 64 mA Sink Current (Com'l), 48 mA (MII) 15 mA Source Current (Com'l), 12 mA (MII)
- $5.0V \pm 10%$  (MII),  $5.0V \pm 5%$  (Commercial)
- Multiple Center Power and Ground Pins
- Designed for use in 40MHz Systems or Better
- Input Clamp Diode to Limit Bus Reflections
- Significantly Improved Switching Characteristics
- Manufactured in 0.7 micron PACE Technology™



## DESCRIPTION

The 'FCT11373 consists of eight latches with 3-state outputs for bus organized system applications. When latch enable (LE) is high the flip-flops appear transparent to the data. Data that meets the required set-up times are latched when LE transitions from HIGH to LOW. Data appears on the bus when the output enable ( $\overline{OE}$ ) is LOW. When output enable is HIGH, the bus output is in the high impedance state, in this mode data may be entered into the latches.

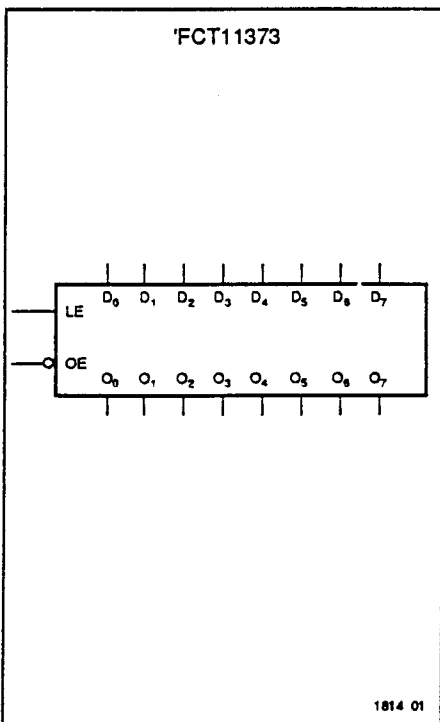
The 'FCT11373 is manufactured with PACE II Technology™ which is Performance Advanced CMOS Engineered with two-level metal and epitaxial substrates to use 0.7 micron effective channel lengths giving 400 picosecond loaded\* internal gate delays. This product incorporates the (lower inductance) multiple center power and ground pinout, hence significantly improving switching characteristics.

This pinout is compatible with P54/74ACT11373.

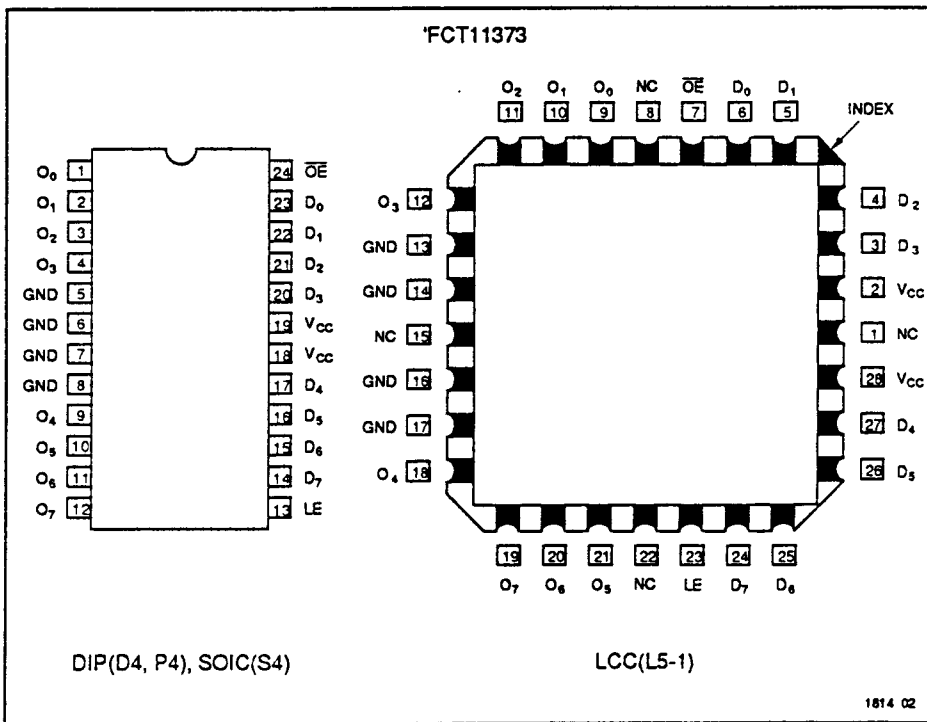
\*For a fan-in/fan-out of 4 at 85°C junction temperature and 3.3V supply.



## LOGIC SYMBOL



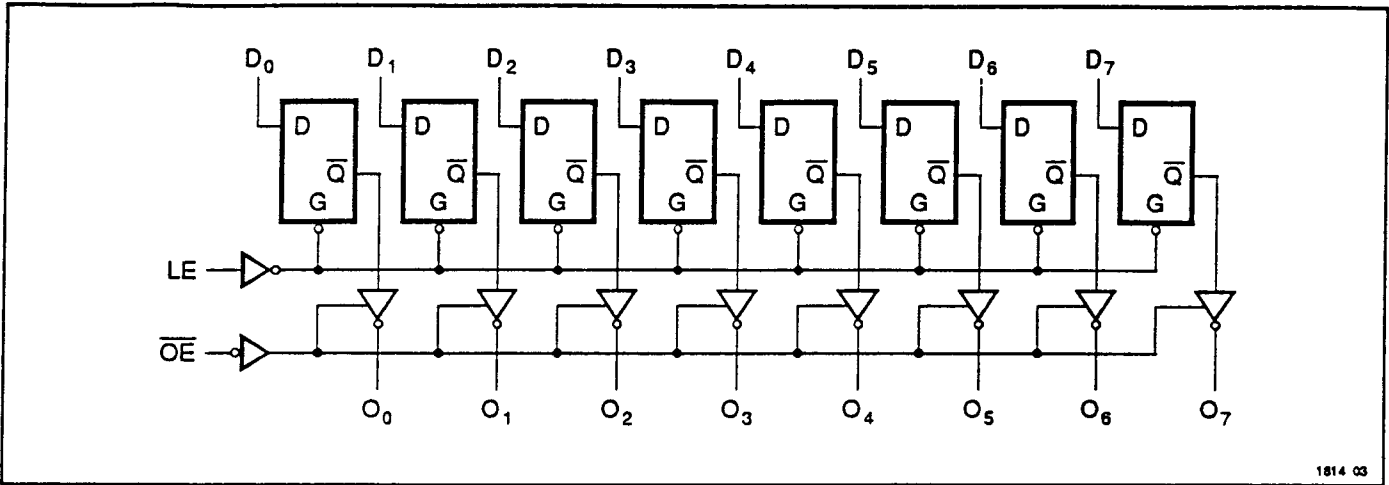
## PIN CONFIGURATIONS



Means Quality, Service and Speed



**LOGIC DIAGRAM**



1814 03

**ABSOLUTE MAXIMUM RATINGS<sup>1,2</sup>**

Symbol	Parameter	Value	Unit
T <sub>STG</sub>	Storage Temperature	-65 to +150	°C
T <sub>A</sub>	Ambient Temperature Under Bias	-65 to +135	°C
V <sub>CC</sub>	V <sub>CC</sub> Potential to Ground	-0.5 to +7.0	V
I <sub>IN</sub>	Input Current	-30 to +5.0	mA

1814 TR 01

- Notes:**
1. Operation beyond the limits set forth in the above table may impair the useful life of the device. Unless otherwise noted, these limits are over the operating free-air temperature range.

Symbol	Parameter	Value	Unit
I <sub>OUTPUT</sub>	Current Applied to Output	120	mA
V <sub>IN</sub>	Input Voltage	-0.5 to V <sub>CC</sub> + 0.5	V
V <sub>OUT</sub>	Voltage Applied to Output	-0.5 to V <sub>CC</sub> + 0.5	V

1814 TR 02

2. Unused inputs must always be connected to an appropriate logic voltage level, preferably either V<sub>CC</sub> or ground.

**RECOMMENDED OPERATING CONDITIONS**

Free Air Ambient Temperature	Min	Max
Military	-55°C	+125°C
Commercial	0°C	+70°C

1814 TR 03

Supply Voltage (V <sub>CC</sub> )	Min	Max
Military	+4.5V	+5.5V
Commercial	+4.75V	+5.25V

1814 TR 04

**DC ELECTRICAL CHARACTERISTICS** (Over recommended operating conditions)

Symbol	Parameter	Min	Typ <sup>1</sup>	Max	Units	V <sub>CC</sub>	Conditions		
V <sub>IH</sub>	Input HIGH Voltage	2.0			V				
V <sub>IL</sub>	Input LOW Voltage			0.8	V				
V <sub>H</sub>	Hysteresis		0.35		V		All inputs		
V <sub>CD</sub>	Input Clamp Diode Voltage		-0.7	-1.2	V	MIN	I <sub>IN</sub> = -18mA		
V <sub>OH</sub>	Output HIGH Voltage	V <sub>CC</sub> = 3V, V <sub>IN</sub> = 0.2V, or V <sub>CC</sub> - 0.2V		V <sub>CC</sub> - 0.2	V <sub>CC</sub>		V	I <sub>OH</sub> = -32μA	
		Military/Commercial (CMOS)		V <sub>CC</sub> - 0.2	V <sub>CC</sub>		V	MIN	I <sub>OH</sub> = -300μA
		Military (TTL)		2.4	4.3		V	MIN	I <sub>OH</sub> = -12mA
		Commercial (TTL)		2.4	4.3		V	MIN	I <sub>OH</sub> = -15mA
V <sub>OL</sub>	Output LOW Voltage	V <sub>CC</sub> = 3V, V <sub>IN</sub> = 0.2V, or V <sub>CC</sub> - 0.2V			GND	0.2	V		I <sub>OL</sub> = 300μA
		Military/Commercial (CMOS)			GND	0.2	V	MIN	I <sub>OL</sub> = 300μA
		Military (TTL)			0.3	0.5	V	MIN	I <sub>OL</sub> = 32mA
		Commercial (TTL)			0.3	0.5	V	MIN	I <sub>OL</sub> = 48mA
		Commercial (TTL)			0.3	0.5	V	MIN	I <sub>OL</sub> = 64mA
I <sub>IH</sub>	Input HIGH Current			5	μA	MAX	V <sub>IN</sub> = V <sub>CC</sub>		
I <sub>IL</sub>	Input LOW Current			-5	μA	MAX	V <sub>IN</sub> = GND		
I <sub>IH</sub>	Input HIGH Current <sup>3</sup>			5	μA	MAX	V <sub>IN</sub> = 2.7V		
I <sub>IL</sub>	Input LOW Current <sup>3</sup>			-5	μA	MAX	V <sub>IN</sub> = 0.5V		
I <sub>ozH</sub>	Off State I <sub>OUT</sub> HIGH-Level Output Current			10	μA	MAX	V <sub>OUT</sub> = V <sub>CC</sub>		
I <sub>ozL</sub>	Off State I <sub>OUT</sub> LOW-Level Output Current			-10	μA	MAX	V <sub>OUT</sub> = GND		
I <sub>ozH</sub>	Off State I <sub>OUT</sub> HIGH-Level Output Current <sup>3</sup>			10	μA	MAX	V <sub>OUT</sub> = 2.7V		
I <sub>ozL</sub>	Off State I <sub>OUT</sub> LOW-Level Output Current <sup>3</sup>			-10	μA	MAX	V <sub>OUT</sub> = 0.5V		
I <sub>OS</sub>	Output Short Circuit Current <sup>2</sup>	-60	-120	-225	mA	MAX	V <sub>OUT</sub> = 0.0V		
C <sub>IN</sub>	Input Capacitance <sup>3</sup>		5	10	pF	MAX	All inputs		
C <sub>OUT</sub>	Output Capacitance <sup>3</sup>		9	12	pF	MAX	All outputs		

**Notes:**

1. Typical limits are at V<sub>CC</sub> = 5.0V, T<sub>A</sub> = +25°C ambient.
2. Not more than one output should be shorted at a time. Duration of short should not exceed one second. The use of high speed test apparatus and/or sample and hold techniques are preferable in order to minimize internal chip heating and more accurately reflect

operational values. Otherwise prolonged shorting of a high output may raise the chip temperature well above normal and thereby cause invalid readings in other parameter tests. In any sequence of parameter tests, I<sub>OS</sub> tests should be performed last.

3. This parameter is guaranteed but not tested.

1814 T01 05

**DC CHARACTERISTICS** (Over recommended operating conditions unless otherwise specified.)

Symbol	Parameter	Typ <sup>1</sup>	Max	Units	Conditions
$I_{CC}$	Quiescent Power Supply Current (CMOS inputs)	0.003	0.5	mA	$V_{CC} = \text{MAX}$ , $f_1 = 0$ , Outputs Open, $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
$\Delta I_{CC}$	Quiescent Power Supply Current (TTL inputs)	0.5	2.0	mA	$V_{CC} = \text{MAX}$ , $V_{IN} = 3.4V^2$ , $f_1 = 0$ , Outputs Open
$I_{CCD}$	Dynamic Power Supply Current <sup>3</sup>	0.15	0.25	mA/ MHz	$V_{CC} = \text{MAX}$ , One Input Toggling, 50% Duty Cycle, $\overline{OE} = \text{GND}$ , $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$ , Outputs Open, $LE = V_{CC}$
$I_C$	Total Power Supply Current <sup>5</sup>	1.7	4.0	mA	$V_{CC} = \text{MAX}$ , $LE = V_{CC}$ , 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 10\text{MHz}$ , $\overline{OE} = \text{GND}$ and $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		2.0	5.0	mA	$V_{CC} = \text{MAX}$ , $LE = V_{CC}$ , 50% Duty Cycle, Outputs Open, One Bit Toggling at $f_1 = 10\text{MHz}$ , $\overline{OE} = \text{GND}$ and $V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$
		3.2	6.5 <sup>4</sup>	mA	$V_{CC} = \text{MAX}$ , $LE = V_{CC}$ , 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$ , $\overline{OE} = \text{GND}$ and $V_{IN} \leq 0.2V$ or $V_{IN} \geq V_{CC} - 0.2V$
		5.2	14.5 <sup>4</sup>	mA	$V_{CC} = \text{MAX}$ , $LE = V_{CC}$ , 50% Duty Cycle, Outputs Open, Eight Bits Toggling at $f_1 = 2.5\text{MHz}$ , $\overline{OE} = \text{GND}$ and $V_{IN} = 3.4V$ or $V_{IN} = \text{GND}$

**Notes:**

- Typical values are at  $V_{CC} = 5.0V$ , +25°C ambient and maximum loading.
- Per TTL driven input ( $V_{IN} = 3.4V$ ); all other inputs at  $V_{CC}$  or GND.
- This parameter is not directly testable, but is derived for use in Total Power Supply calculations.
- Values for these conditions are examples of the  $I_{CC}$  formula. These limits are guaranteed but not tested.
- $I_C = I_{\text{QUIESCENT}} + I_{\text{INPUTS}} + I_{\text{DYNAMIC}}$   
 $I_C = I_{CC} + \Delta I_{CC} D_H N_T + I_{CCD} (f_1/2 + f_1 N_1)$   
 $I_{CC}$  = Quiescent Current with CMOS input levels

- $\Delta I_{CC}$  = Power Supply Current for a TTL High Input ( $V_{IN} = 3.4V$ )
- $D_H$  = Duty Cycle for TTL Inputs High
- $N_T$  = Number of TTL Inputs at  $D_H$
- $I_{CCD}$  = Dynamic Current Caused by an Input Transition Pair (HLH or LHL)
- $f_0$  = Clock Frequency for Register Devices (Zero for Non-Register Devices)
- $f_1$  = Input Frequency
- $N_1$  = Number of Inputs at  $f_1$
- All currents are in milliamps and all frequencies are in megahertz.

1814 TR 06

**FUNCTION TABLE (Each Latch)**

Inputs			Outputs 'FCT11373
$\overline{OE}$	LE	D	O
L	H	H	H
L	H	L	L
L	L	X	$Q_0$
H	X	X	Z

- H = HIGH Voltage Level
- L = LOW Voltage Level
- X = Don't Care
- Z = HIGH Impedance
- $Q_0$  = previous state of flip flops ( $Q_{n-1}$ )

1814 TR 07

## AC CHARACTERISTICS

Symbol	Parameter	'FCT11373				Units	Fig. No.
		MIL		COM'L			
		Min. <sup>1</sup>	Max.	Min. <sup>1</sup>	Max.		
$t_{PLH}$ $t_{PHL}$	Propagation Delay $D_n$ to $O_n$	—	—	1.0	3.6	ns	1, 3
$t_{PLH}$ $t_{PHL}$	Propagation Delay LE to $O_n$	—	—	1.0	6.5	ns	1, 5
$t_{PZH}$ $t_{PZL}$	Output Enable Time	—	—	1.0	5.0	ns	1 7
$t_{PHZ}$ $t_{PLZ}$	Output Disable Time	—	—	1.0	4.5	ns	8

1814 Tbl 08

## AC OPERATING REQUIREMENTS

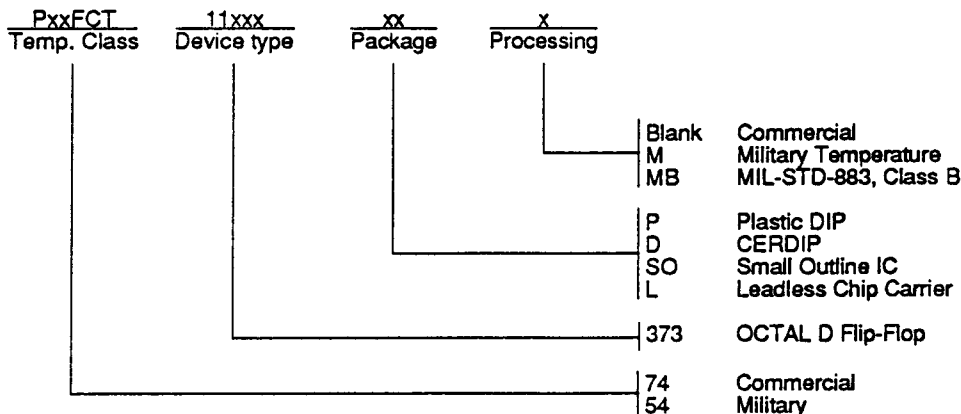
Symbol	Parameter	'FCT11373				Units	Fig. No.
		MIL		COM'L			
		Min. <sup>1</sup>	Max.	Min. <sup>1</sup>	Max.		
$t_s(H)$ $t_s(L)$	Setup Time, High to Low $D_n$ to LE	—	—	2.0	—	ns	9
$t_n(H)$ $t_n(L)$	Hold Time, High to Low $D_n$ to LE	—	—	1.5	—	ns	
$t_w(H)$	LE Pulse Width High	—	—	5.0	—	ns	5

1814 Tbl 09

## Note:

1. Minimum limits are guaranteed but not tested on Propagation Delays.  
AC Characteristics guaranteed with  $C_L = 50$  pF as shown in Figure 1.

## ORDERING INFORMATION



1813 05